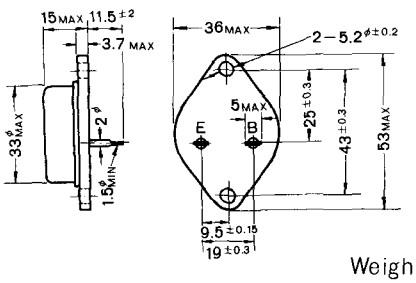
POWER TRANSISTOR

	Type	P_C (W)	I_C (A)	I_B (A)	V_{CBO} (V)	V_{CEO} (V)	V_{CES} (V)	h_{FE} (STD)	f_{ae} (kHz)	T_j (°C)	Dimensions
Germanium transistor	2SB205	80	−20	−3	− 80	—	−60	40	2.5	85	Fig.26 (For low-frequency power amplification)
	2SB206		−30		− 80		−60	100			
	2SB207		−20		−100		−75	40			
	2SB208		−30		−100		−75	100			
	2SB207A		−20		−140		−85	40			
	2SB208A		−30		−140		−85	100			
	2SB211	80	−20	−3	− 80	—	−60	40	2.5	85	Fig.26 (For low-frequency power switching)
	2SB212		−30		− 80		−60	100			
	2SB213		−20		−100		−75	40			
	2SB214		−30		−100		−75	100			
	2SB213A		−20		−140		−85	40			
	2SB214A		−30		−140		−85	100			
Silicon transistor	2SC407	100	10	3	150	100	—	20	400	150	Fig.27
	2SC408				150	100		40			
	2SC409				200	140		20			
	2SC410				200	140		40			
	2SC411				300	200		20			
	2SC412				300	200		40			
	2SD206	150	10	4	50	30	—	20	18	150	Fig.27
	2SD207				100	60					
	2SD208				150	90					
	2SC431	200	30	10	150	100	—	20	400	150	Fig.28
	2SC432				150	100		40			
	2SC433				200	140		20			
	2SC434				200	140		40			
	2SC435				300	200		20			
	2SC436				300	200		40			
High voltage silicon transistor	2SC1466	30	3	1	450	360(sus)	—	16	f_T 10 (MHz)	150	Fig.29
	2SC1467				500	400(sus)		12			
	2SC1468	100	100	4	450	360(sus)	—	16	f_T 10 (MHz)	150	Fig.27
	2SC1469				500	400(sus)		12			
	2SC1470	200	200	10	450	360(sus)	—	20	f_T 10 (MHz)	150	Fig.28
	2SC1471				500	400(sus)		15			
Darlington silicon transistor	2SD384	30	7	0.5	80	80(sus)	—	5000	20	150	Fig.29
	2SD385				100	100(sus)					

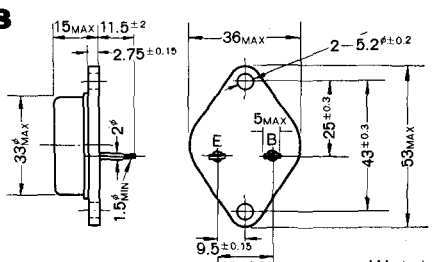
Unit : mm

Fig.26



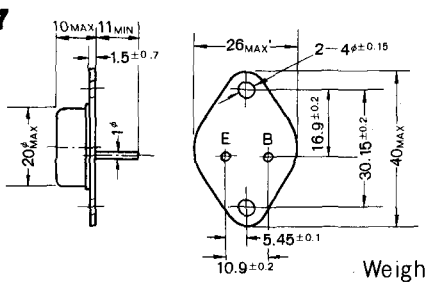
Weight: 44(g)

Fig.28



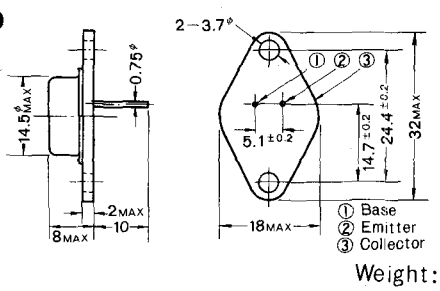
Weight: 44(g)

Fig.27



Weight: 17(g)

Fig.29



Weight: 6.3(g)